

Features

- Ultra Low G-Sensitivity
- · Low Phase Noise
- Very High Frequency
- Frequency Range: 50 MHZ to 250 MHZ
- Standard Frequency: 100 MHz
- Vibration Compensation

Applications

- Military Avionics
- · Airborne Radar
- Test Equipment
- Frequency Synthesizers
- Position Location
- Satellite Communications

Performance Specifications

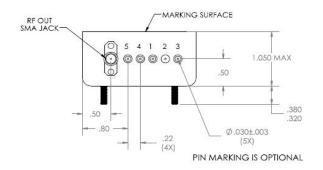
Parameter	Min	Тур	Max	Units	Condition		
Available Frequencies							
Frequency Range	50		250	MHz			
	G-Sensitivity Performance						
standard crystal			1.5	ppb/g			
g-Sensitivity w\ Low g-Crystal			0.5	ppb/g			
g-Sensitivity w\ Low g-Crystal & Vibration compensation			0.05	ppb/g	Degrades to 0.5 ppb/g above 250 Hz		
(No mechanical resonances out to 2KHz)					G sensitivity specified per axis		
For oscillators with 0.2 ppb/g out to 2 KHz	please co	ntact fa	ctory.				
			ency Sta				
(Stabilities listed for 100 MHz. F	or Stabil	lities abo	ove 100 l	MHz values	s may degrade. Please contact factory.)		
vs. Operating Temperature Range	-200		+200	ppb	-40… +85°C		
(referenced to +25°C)	-150		+150	ppb	-40 +70°C		
	-100		+100	ppb	-20 +70°C		
	-50		+50	ppb	0 +70°C		
Initial Tolerance	-500		+500	ppb	at time of shipment, nominal EFC		
vs. Supply Voltage Change	-10		+10	ppb	Vs ± 5%		
vs. Load Change	-10		+10	ppb	Load ± 5%		
vs. Aging / Daily	-5		+5	ppb	after 30 days operation		
vs. Aging / 1 st Year	-200		+200	ppb	after 30 days operarion		
vs. Aging / 10 Year	-1.5		+1.5	ppm	after 30 days operation		
Retrace ²	-200		+200	ppb			
Warm-up Time			5	minutes	to ± 100ppb of final frequency (2 hour reading) @ +25°C		

Performance Specifications

Parameter	Min	Тур	Max	Units	Condition		
Supply Voltage (Vs)							
Supply voltage	14.25	15.0	15.75	VDC	ordering code A		
	11.4	12.0	12.6	VDC	oredering code B		
			10.0	Watts	during warm-up all temperatures		
O Daving Communities			3.5	Watts	steady state @ +25°C		
Oven Power Consumption			7.0	Watts	steady state @ -40°C		
			1.0	Watts	steady state @ +70°C		
			RF Outp	ut			
Start Time		1	2	S	time required to achieve 90% of amplitude		
Signal		Sin	ewave				
Load		50		Ohm			
Output Power	+7.0	+10	+13	dBm			
Harmonics			-30	dBc			
Subharmomics			-30	dBc	for oscillator with output frequency > 120 MHz		
		Freque	ncy Tun	ing (EFC)			
Tuning Range	±1.5		±3.0	ppm	Electronic frequency control		
Linearity			20	%			
Tuning Slope		Pc	sitive				
Control Voltage Range	0.0	+4.0	+8.0	VDC			
Input Impedance	20			kOhm			
Modulation Bandwidth	150			Hz			
	Λ	/lechani	cal Trim	(Internal)			
Tuning Range	±1.5		±3.0	ppm	Internal Mechanical		
		Р	hase No	ise			
Phase Noise ³ (@ 100 MHZ) (under static conditions - no vibration)			-100 -130 -150 -165 -175	dBc/Hz dBc/Hz dBc/Hz dBc/Hz dBc/Hz	10 Hz 100 Hz 1 KHz 10 KHz 100 KHz		
Phase Noise ³ (@ 200 MHZ) (under static conditions - no vibration)			-90 -120 -140 -155 -165	dBc/Hz dBc/Hz dBc/Hz dBc/Hz dBc/Hz	10 Hz 100 Hz 1 KHz 10 KHz 100 KHz		

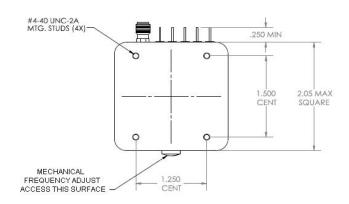
Parameter	Min	Тур	Max	Units	Condition		
Additional Parameters ¹							
Weight			150	g			
	Absolute Maximum Ratings						
Supply voltage (Vs)			28	V			
Output Load	25		open	ohm			
Operable Temperature Range	-55		+85	°C			
	En	vironm	ental Sp	ecificatio	าร		
Shock (Operating)	MIL-STE)-202, Me	ethod 213	, Condition	J, 30G, 11ms, half sine		
Shock (Endurance)	Mil-STD	-202, Me	thod 213	, Condition	C, 100G, 6ms, half sine		
Sine Vibration (Operating)	Mil-STD	Mil-STD-202, Method 204, Condition C, 10 G					
Sine Vibration (Endurance)	Mil-STD	Mil-STD-202, Method 204, Condition D, 20 G					
Random Vibration (Operating)	Mil-STD-202, Method 214, Condition I-C, 9.26 Grms, 3-5min/axis (without vibe comp) Mil-STD-202, Method 214, Condition I-A, 5.35 Grms, 3-5min/axis (with vibe comp)						
Random Vibration (Endurance)	Mil-STD	-202, Me	thod 214	, Condition	l-D, 11.95 Grms, 3hrs/axis		
Seal	Nonhermetic - Mil-STD-202, Method 112, Condition D available only as custom part number - please contact factory						
Humidity	MIL-STD-202, Method 103, Condition B, 90% rh						
Altitude	MIL-STD-202, Method 105, sea level to 30,000 ft						
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition A,B,C						
RoHS	not RoHS compliant						
Terminal Strength	MIL-STD-202, Method 211, Condition C (5 bends at 45°, 2 lbs)						
Moisture Sensitivity Level	1						
Storage Temperature Range	-55		+125	°C			

Outline Drawing / Enclosure

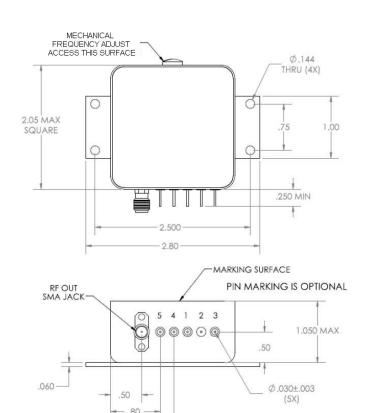


Dimensions in inches

Package configuration A			
ordering code	Height "H"		
5	0.80		
0	1.05		



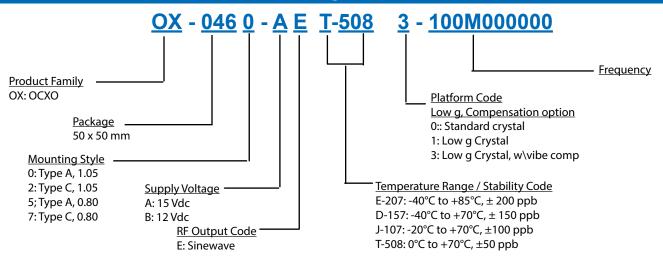
	Pin Connections
1	Electronic Frequency Control (EFC)
2	Ground (Case)
3	Supply Voltage
4	Microsemi Internal Use Only / NC
5	Microsemi Internal Use Only / NC



Package configuration C				
ordering code	Height "H"			
7	0.80			
2	1.05			

	Pin Connections
1	Electronic Frequency Control (EFC)
2	Ground (Case)
3	Supply Voltage
4	Microsemi Internal Use Only / NC
5	Microsemi Internal Use Only / NC

Ordering Information⁴



Additional Ordering Options

Additional ordering options available include custom temperature ranges, custom temperature stabilities, custom phase noise requirements, low profile, custom supply voltage, hermetic option and improved g-sensitivity. These modifications require a custom dash number - please contact the factory for additional information.

Design Tools

Microsemi stocks the following items for small orders and prototype development:
OX-0467-AEE-2073-100M00000
Microsemi stocks the following evaluation board for this product:
None
Application Notes:
None

Notes:

- 1. Unless otherwise stated, all values are valid after warm-up time and refer to typical conditions for supply voltage, frequency control voltage, load, and temperature (25°C).
- 2. Retrace is defined as the frequency difference between the end of two 24 hour on power periods with a 24 hour off period in between while at a constant temperature.
- 3. Phase noise degrades with increasing output frequency.
- 4. Not all options and codes available at all frequencies.



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